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1 ABSTRACT OF THE DISCLOSURE

 A semiconductor device includes a substrate,
a gate oxide film formed on the substrate, a gate
electrode provided on the gate oxide film, first and
5 second diffusion regions formed in the substrate at
both lateral sides of the gate electrode. The gate
electrode includes a first region located immediately
underneath the gate electrode and a second region
adjacent to the first region, wherein the first and
10 second regions contain N atoms with respective
concentrations such that the second region contains N
with a higher concentration as compared with the first
region.

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